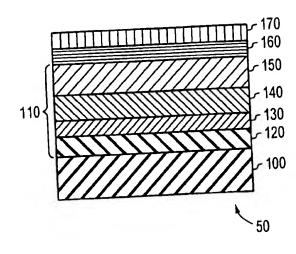
Title: Semiconductor Heterostructures and Related Methods
Inventor(s): Leitz et al.
Atty Docket No. ASC-058A
Filing Date: August 22, 2003
Atty/Agent: MLBeloborodov/BRChase
Formal Drawings



1/6



See 2/3/st

FIG. 1

Title: Semiconductor Heterostructures and Related Methods
Inventor(s): Leitz et al.
Atty Docket No. ASC-058A
Filing Date: August 22, 2003
Atty/Agent: MLBeloborodov/BRChase
Formal Drawines

Formal Drawings

2/6

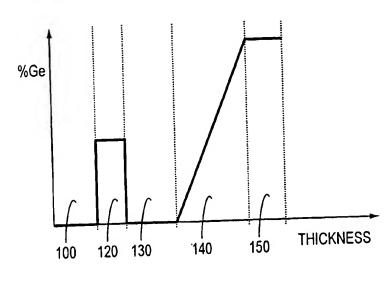


FIG. 2

approved Lie 2/3/25

Methods

Methods Inventor(s): Leitz et al. Atty Docket No. ASC-058A Filing Date: August 22, 2003 Atty/Agent: MLBeloborodov/BRChase Formal Drawings

3/6

	QUALITATIVE EVALUATION OF DISLOCATION PILE-UP DENSITY			
% Ge	H* = 0.6 T <sub>crit</sub>	H = 1.25 T <sub>crit</sub>	H = 2 T <sub>crit</sub>	H = 5 T <sub>crit</sub>
5	HIGH	MEDIUM	LOW	LOW
10	HIGH	MEDIUM	MEDIUM	LOW
15	HIGH	MEDIUM	MEDIUM	LOW

\* THICKNESS (H) OF THE SEED LAYER RELATIVE TO ITS CRITICAL THICKNESS (T<sub>crit</sub>).

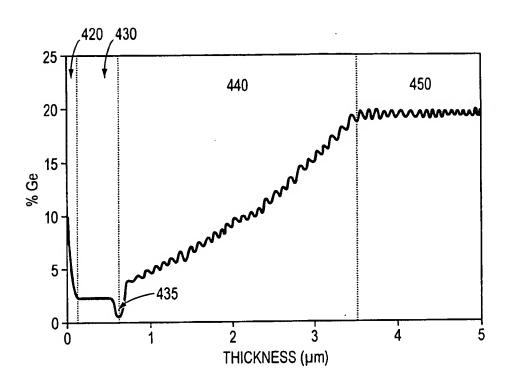
FIG. 3

spproved Lee

Methods

Inventor(s): Leitz et al.
Atty Docket No. ASC-058A
Filing Date: August 22, 2003
Atty/Agent: MLBeloborodov/BRChase
Formal Drawings

4/6



approved Lee 2/25

FIG. 4

Methods

Inventor(s): Leitz et al.
Atty Docket No. ASC-058A
Filing Date: August 22, 2003
Atty/Agent: MLBeloborodov/BRChase

Formal Drawings

5/6

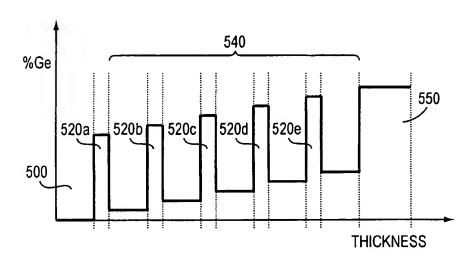


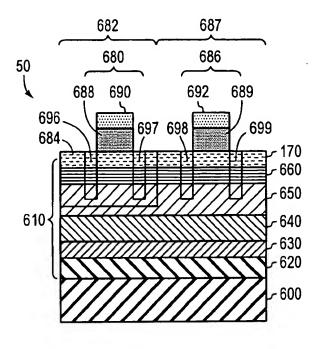
FIG. 5

approved for 2/3/05

Methods

Inventor(s): Leitz et al.
Atty Docket No. ASC-058A
Filing Date: August 22, 2003
Atty/Agent: MLBeloborodov/BRChase
Formal Drawings

6/6



approved Lee 2/3/05

+

FIG. 6